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P-Channel 100-V (D-S) MOSFET

PRODUCT SUMMARY					
V _{DS} (V)	$R_{DS(on)}(\Omega)$	I _D (A)	Q _g (Typ.)		
- 100	0.450 at V _{GS} = - 10 V	-1.5	8.1		
	0.557 at V _{GS} = - 4.5 V	-1.2	0.1		

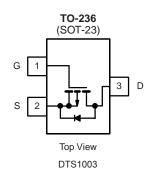
FEATURES

- Halogen-free According to IEC 61249-2-21 Available
- TrenchFET[®] Power MOSFET
- Ultra Low On-Resistance
- Small Size



APPLICATIONS

• Active Clamp Circuits in DC/DC Power Supplies



ABSOLUTE MAXIMUM RATINGS	$T_A = 25$ °C, unle	ss otherwise r	noted		
Parameter		Symbol	LIMIT	Unit	
Drain-Source Voltage		V _{DS}	- 100	.,,	
Gate-Source Voltage		V_{GS}	± 20	V	
Continuous Dunis Courset /T 450 90\8 h	T _A = 25 °C	1	- 1.5		
Continuous Drain Current (T _J = 150 °C) ^{a, b}	T _A = 70 °C	- I _D	- 1.2		
Pulsed Drain Current		I _{DM}	- 4.5	Α	
Continuous Source Current (Diode Conduction) ^{a, b}		I _S	- 6.8		
Avalanche Current	L = 1.0 mH	I _{AS}	2.2		
Avalanche Energy	L = 1.0 Min	E _{AS}	1.31	mJ	
Mariana Bana Birata da ah	T _A = 25 °C	P _D	0.75	W	
Maximum Power Dissipation ^{a, b}	T _A = 70 °C	' D	0.48	VV	
Operating Junction and Storage Temperature Range		T _J , T _{stg}	- 55 to 150	°C	

THERMAL RESISTANCE RATINGS						
Parameter		Symbol	Typical	Maximum	Unit	
Maximum Junction-to-Ambient ^a	t ≤ 5 s	R _{thJA}	85	150	°C/W	
	Steady State		140	186		
Maximum Junction-to-Foot (Drain)	Steady State	R _{thJF}	45	60]	

Notes:

- a. Surface Mounted on 1" x 1" FR4 board.
- b. Pulse width limited by maximum junction temperature.



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			Limits				
Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit	
Static							
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0 \text{ V}, I_{D} = -250 \mu\text{A}$	- 100			V	
Gate-Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = -250 \mu A$	- 1.2		- 2.5	ľ	
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			± 100	nA	
Zero Gate Voltage Drain Current	I _{DSS} -	V _{DS} = - 80 V, V _{GS} = 0 V			- 1	μА	
		V _{DS} = -80 V, V _{GS} = 0 V, T _J = 55 °C			- 10		
On-State Drain Current ^a	I _{D(on)}	$V_{DS} \le -15 \text{ V}, V_{GS} = 10 \text{ V}$	- 2.6			Α	
	Б	$V_{GS} = -10 \text{ V}, I_D = -0.5 \text{ A}$		0.45	0.60	Ω	
Drain-Source On-Resistance ^a	R _{DS(on)}	$V_{GS} = -4.5 \text{ V}, I_D = -0.5 \text{ A}$		0.557	0.75		
Forward Transconductance ^a	9 _{fs}	V _{DS} = - 15 V, I _D = - 0.5 A		2.1		S	
Diode Forward Voltage	V_{SD}	I _S = - 1.0 A, V _{GS} = 0 V		0.5	- 1.2	V	
Dynamic ^b	•		•	•			
Total Gate Charge	Q_g	V _{DS} = -80 V, V _{GS} = 10 V,		8.1	13		
Gate-Source Charge	Q _{gs}	$I_{DS} = -0.5 \text{ A}$		1.6		nC	
Gate-Drain Charge	Q _{gd}			2.4			
Gate Resistance	R_g	f = 1.0 MHz		10		Ω	
Input Capacitance	C _{iss}			570	689		
Output Capacitance	C _{oss}	$V_{DS} = -25 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$		136		pF	
Reverse Transfer Capacitance	C _{rss}			27			
Switching ^c							
Torre On Time	t _{d(on)}			8			
Turn-On Time	$V_{DD} = -75 \text{ V}, R_L = 75 \Omega$ $I_D \cong -1.0 \text{ A}, V_{GEN} = -10 \text{ V}$		14		ne		
Turn O# Time	t _{d(off)}	$R_{a} = 6 \Omega$		17		ns	
Turn-Off Time	t _f	g – • 22		11			
Body Diode Reverse Recovery Charge	Q _{rr}	$I_F = 0.5 \text{ A}, dI/dt = 100 \text{ A/}\mu\text{s}$		90		nC	

Notes:

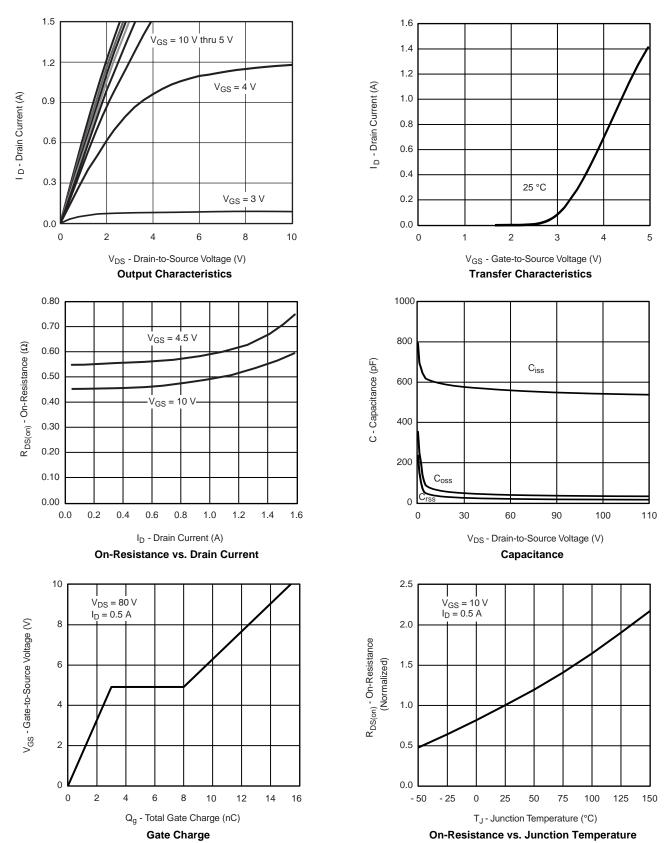
- a. Pulse test: PW \leq 300 μs duty cycle \leq 2 %.
- b. For DESIGN AID ONLY, not subject to production testing.
- c. Switching time is essentially independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.





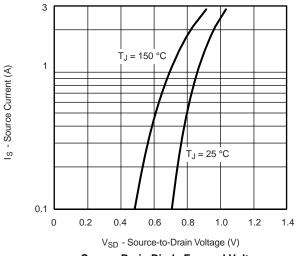
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



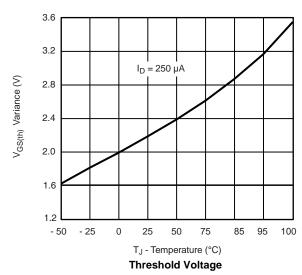


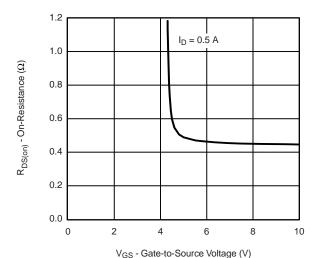


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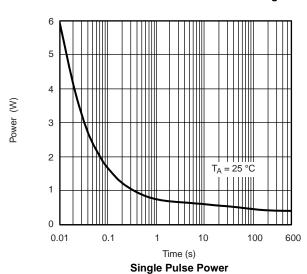


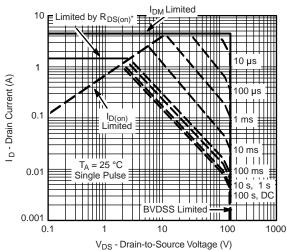
Source-Drain Diode Forward Voltage





On-Resistance vs. Gate-to-Source Voltage



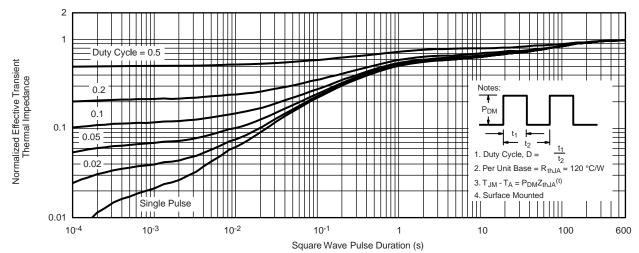


* V_{GS} > minimum V_{GS} at which R_{DS(on)} is specified

Safe Operating Area



THERMAL RATINGS (T_A = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient





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